



**THE DATASHEET OF
DMN2026UVT-13**



Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D $T_A = +25^\circ C$
20V	24m Ω @ $V_{GS} = 4.5V$	6.2A
	32m Ω @ $V_{GS} = 2.5V$	

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Backlighting

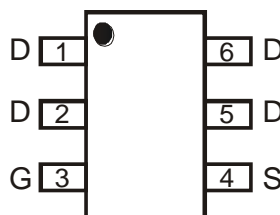
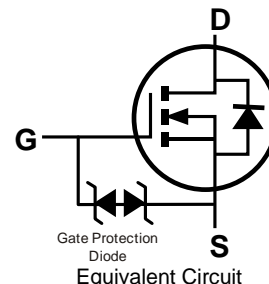
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.013 grams (Approximate)

TSOT26



Top View

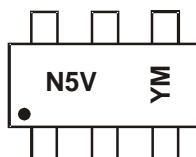

 Top View
Pin Configuration

 Gate Protection
Diode
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2026UVT-7	TSOT26	3,000/Tape & Reel
DMN2026UVT-13	TSOT26	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N5V = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	± 10	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State $T_A = +25^\circ\text{C}$ I_D	6.2	A
Maximum Body Diode Forward Current (Note 6)	I_S	2	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	20	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.15	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	107	$^\circ\text{C/W}$
	$t < 10\text{s}$	76	
Total Power Dissipation (Note 6)	P_D	1.75	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	75	$^\circ\text{C/W}$
	$t < 10\text{s}$	50	
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	16	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	—	1.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	18	24	m Ω	$V_{GS} = 4.5\text{V}, I_D = 6.2\text{A}$
		—	21	32		$V_{GS} = 2.5\text{V}, I_D = 5.2\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1.3\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	—	887	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{OSS}	—	91	—		
Reverse Transfer Capacitance	C_{RSS}	—	37	—		
Gate Resistance	R_g	—	191	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	10	—	nC	$V_{DS} = 10\text{V}, I_D = 6.5\text{A}$
Total Gate Charge ($V_{GS} = 8\text{V}$)	Q_g	—	18.4	—		
Gate-Source Charge	Q_{gs}	—	1.3	—		
Gate-Drain Charge	Q_{gd}	—	1.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	53	—	ns	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V},$ $R_G = 6\Omega, R_L = 10\Omega, I_D = 1\text{A}$
Turn-On Rise Time	t_R	—	66	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	619	—		
Turn-Off Fall Time	t_F	—	197	—		
Reverse Recovery Time	t_{RR}	—	119	—	ns	$I_F = 4\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	96	—	nC	$I_F = 4\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1 inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

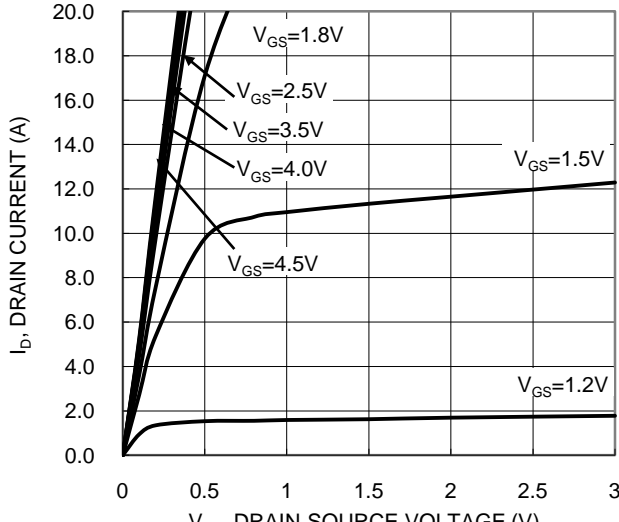


Figure 1. Typical Output Characteristic

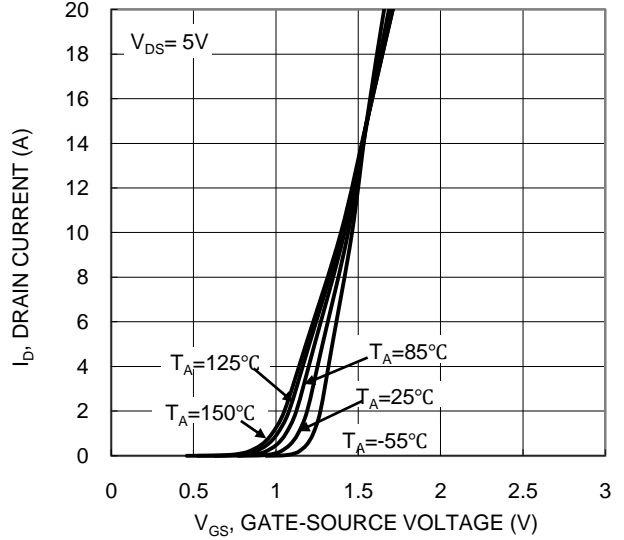


Figure 2. Typical Transfer Characteristic

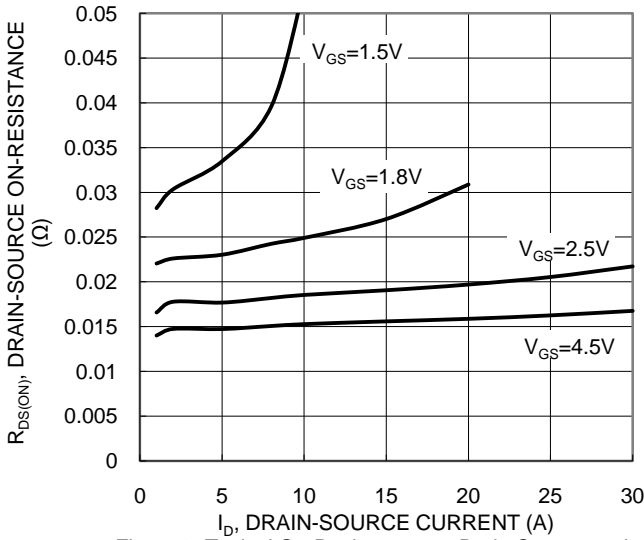


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

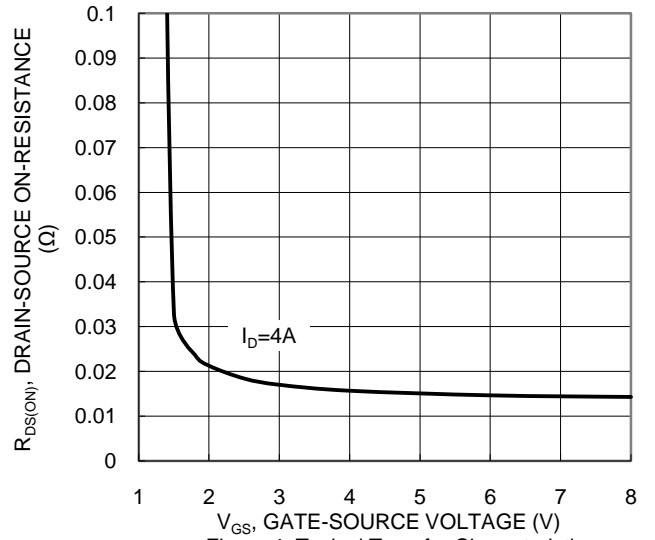


Figure 4. Typical Transfer Characteristic

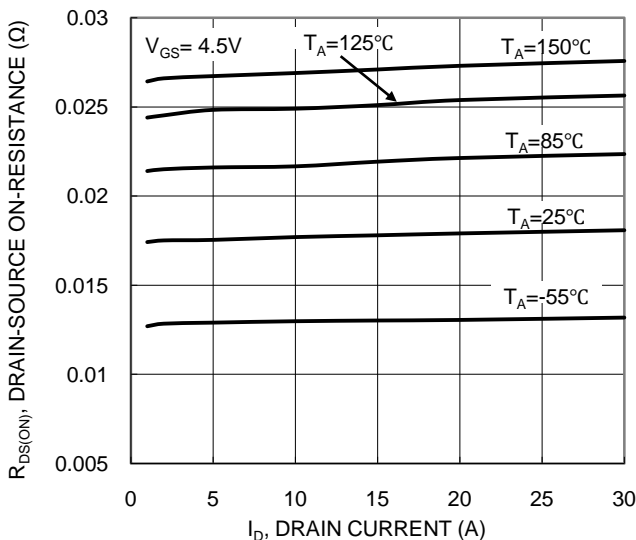


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

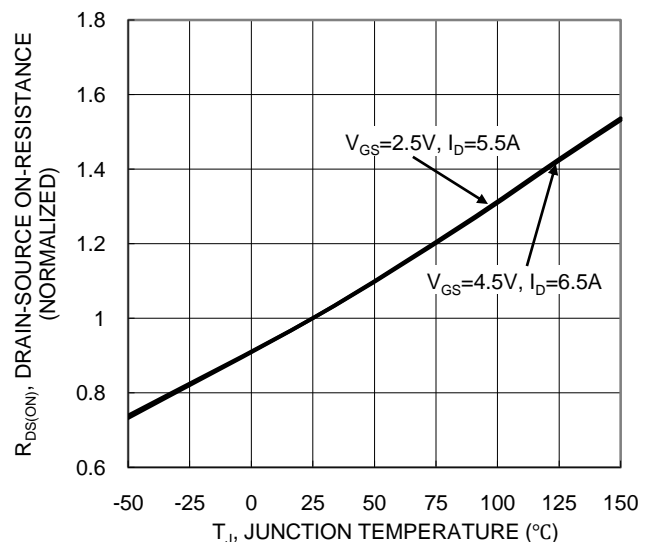


Figure 6. On-Resistance Variation with Temperature

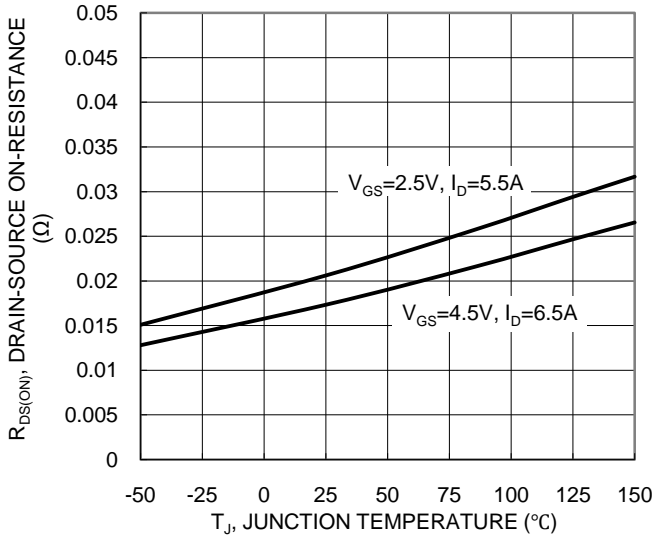


Figure 7. On-Resistance Variation with Temperature

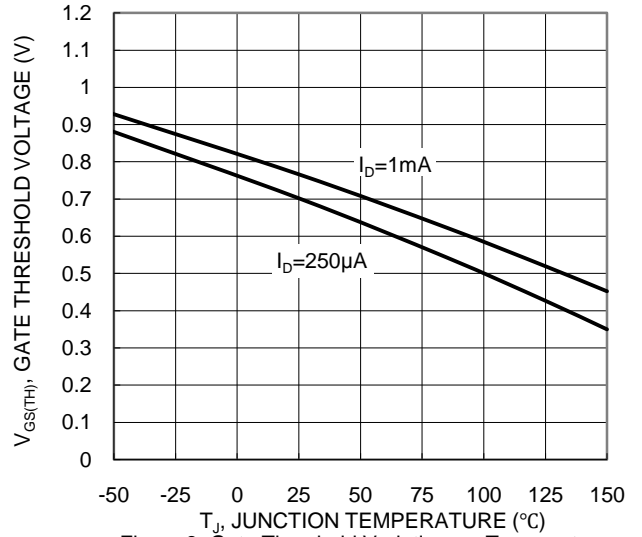


Figure 8. Gate Threshold Variation vs. Temperature

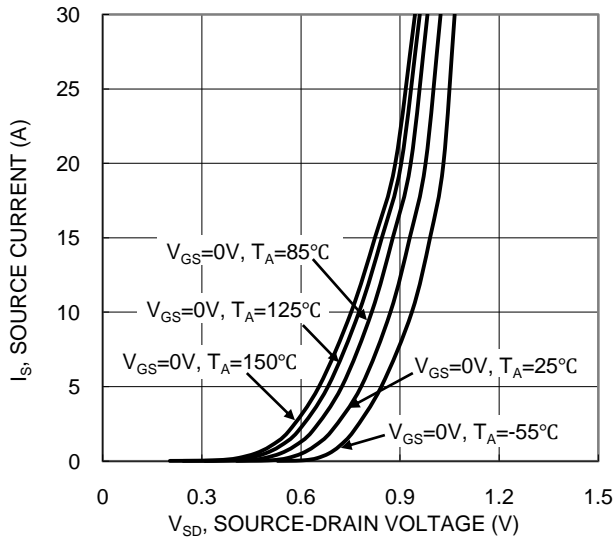


Figure 9. Diode Forward Voltage vs. Current

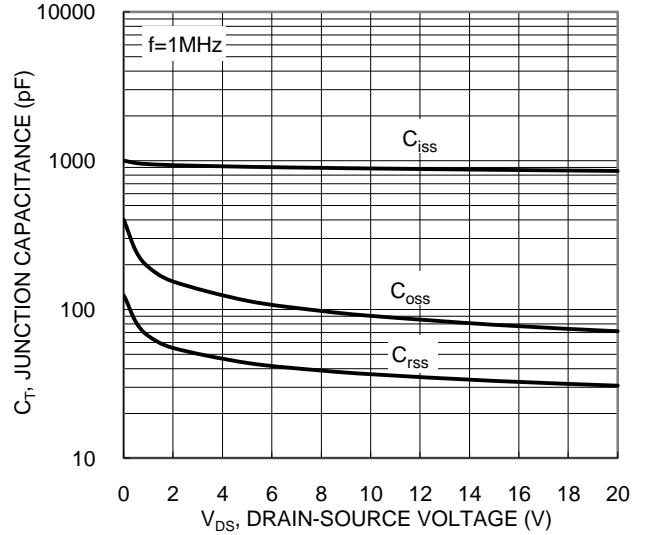


Figure 10. Typical Junction Capacitance

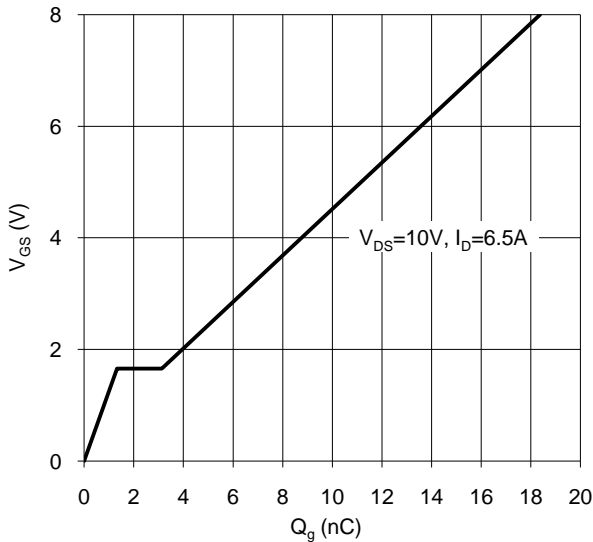


Figure 11. Gate Charge

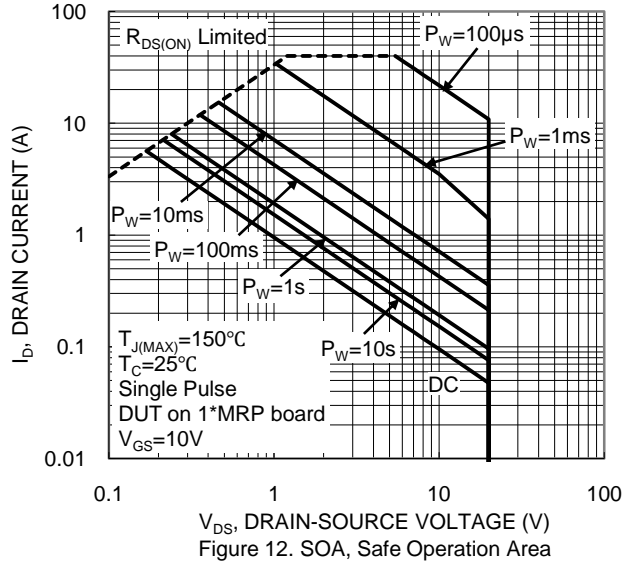


Figure 12. SOA, Safe Operation Area

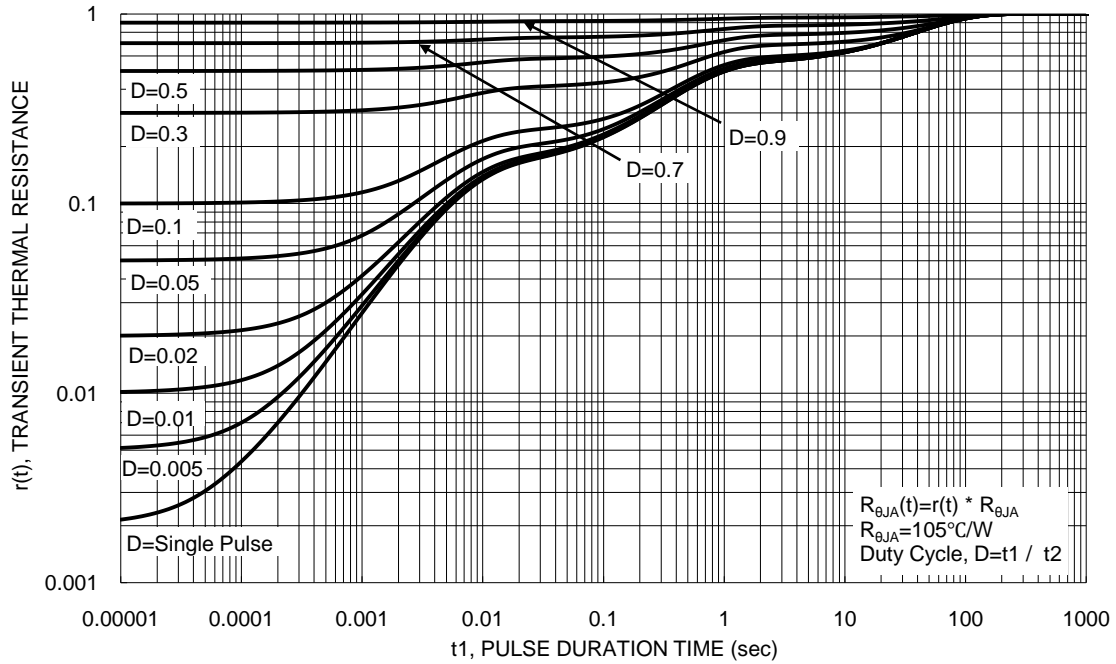
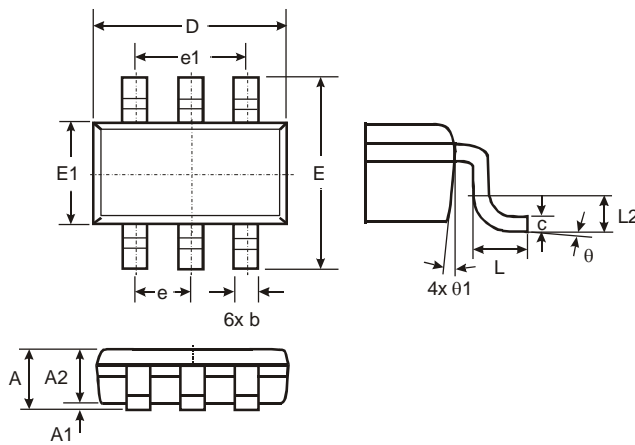


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

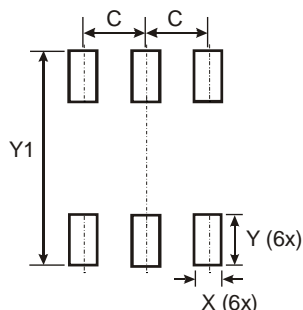
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.01	0.10	—
A2	0.84	0.90	—
D	—	—	2.90
E	—	—	2.80
E1	—	—	1.60
b	0.30	0.45	—
c	0.12	0.20	—
e	—	—	0.95
e1	—	—	1.90
L	0.30	0.50	—
L2	—	—	0.25
θ	0°	8°	4°
θ_1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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